



SANYO Semiconductors

DATA SHEET

2SC3689

NPN Epitaxial Planar Silicon Transistor

High-hFE, Low-Frequency General-Purpose Amplifier Applications

Applications

- Low-frequency general-purpose amplifiers, drivers, muting circuit.

Features

- Small Cob (Cob=1.5pF).
- Ultrasmall-sized package permitting 2SC3689-used sets to be made smaller, slimmer.
- Adoption of MBIT process.
- High DC current gain (hFE=800 to 3200).
- Low collector-to-emitter saturation voltage ($V_{CE(sat)} \leq 0.5V$).
- High V_{EBO} (V_{EBO} ≥ 15V).

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		60	V
Collector-to-Emitter Voltage	V _{CEO}		50	V
Emitter-to-Base Voltage	V _{EBO}		15	V
Collector Current	I _C		100	mA
Collector Current (Pulse)	I _{CP}		200	mA
Collector Dissipation	P _C		200	W
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

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2SC3689

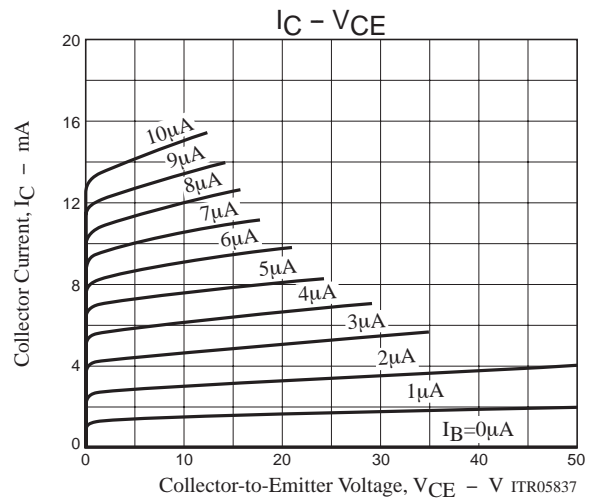
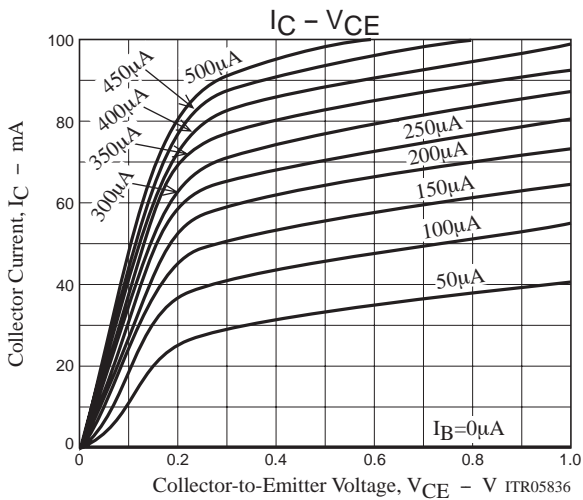
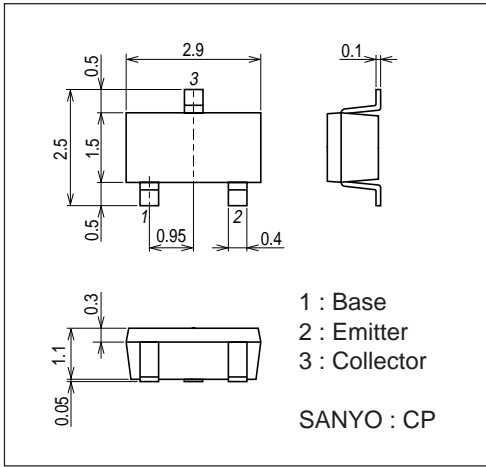
Electrical Characteristics at Ta=25°C

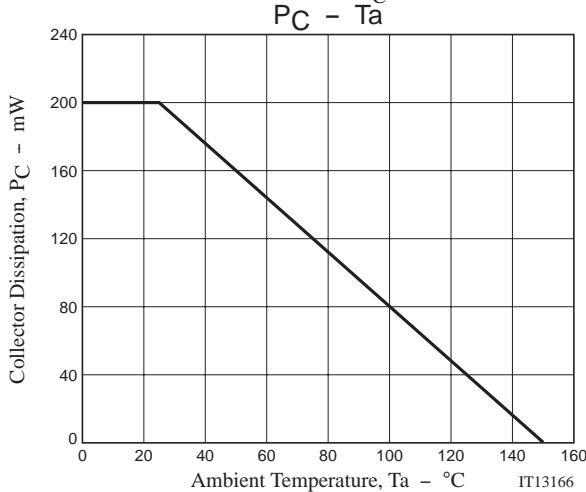
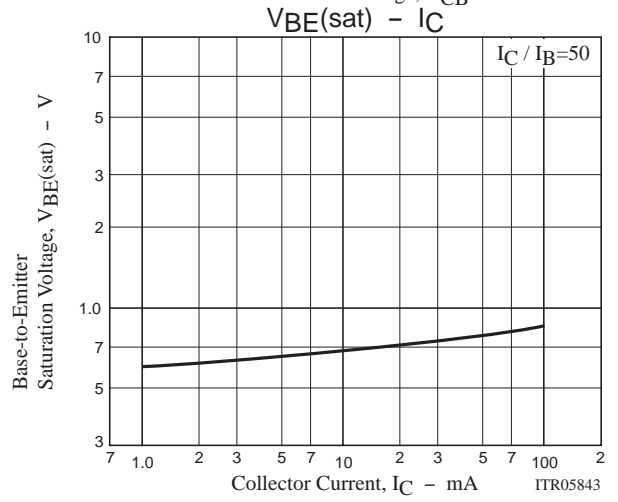
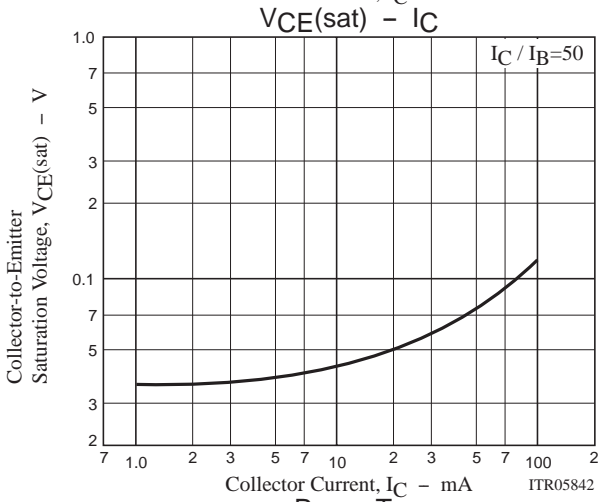
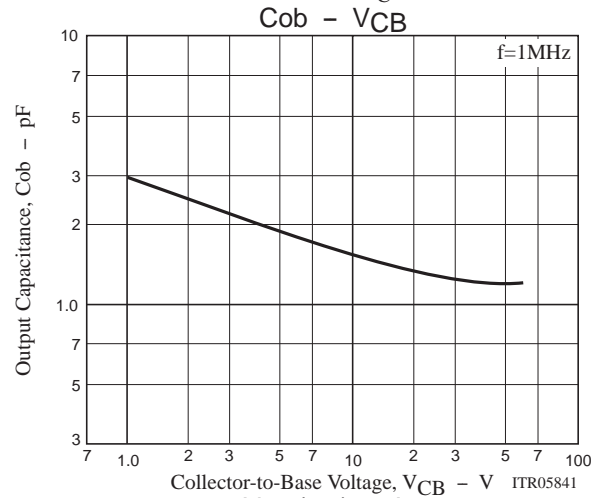
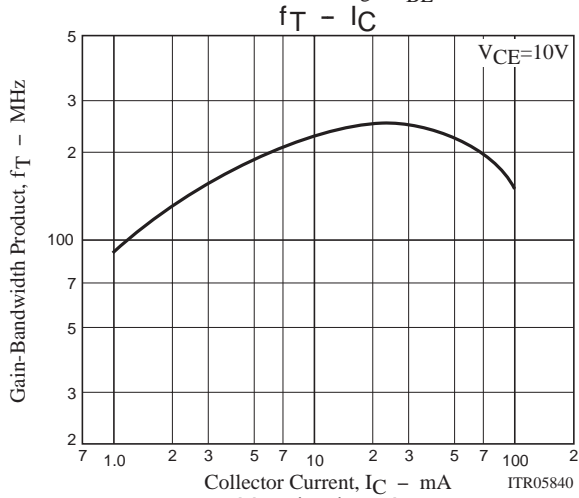
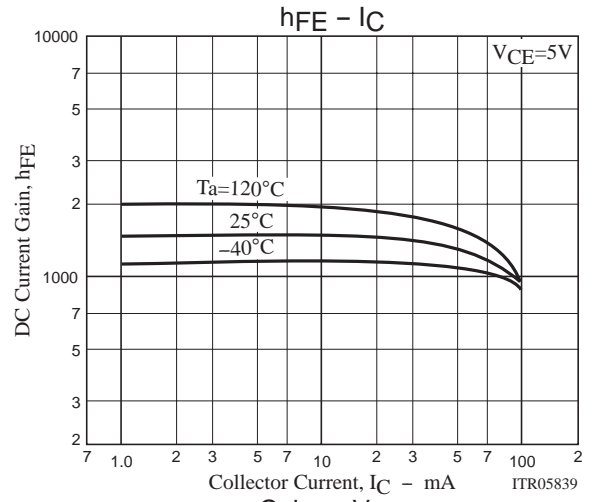
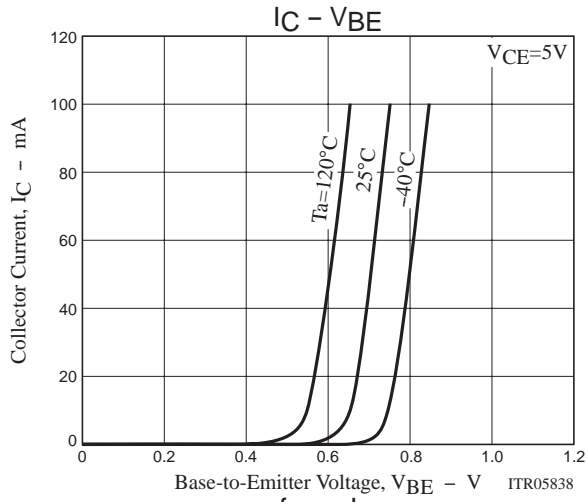
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=40V, I_E=0A$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=10V, I_C=0A$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=10mA$	800	1500	3200	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=10mA$		200		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		1.5		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=1mA$		0.1	0.5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=1mA$		0.8	1.1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0A$	60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0A$	15			V

Package Dimensions

unit : mm (typ)

7013A-009





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